

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Robert H. Dennard, et al. **Examiner:** Unassigned
Serial No.: To be assigned **Art Unit:** Unassigned
Filed: Herewith **Docket:** YOR920020157US2(15667A)
For: POLYSILICON BACK-GATED
SOI MOSFET FOR DYNAMIC THRESHOLD
VOLTAGE CONTROL **Dated:** September 11, 2003

Commissioner for Patents
United States Patent and Trademark Office
P.O. Box 1450
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PRELIMINARY AMENDMENT

Sir:

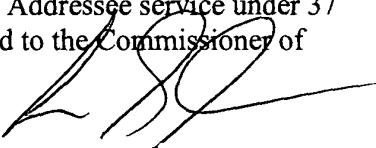
In connection with filing the above-identified patent application under 37 C.F.R. §1.53(b), applicants submit the following amendments and remarks for entry of record in the above-identified patent application.

CERTIFICATE OF MAILING BY EXPRESS MAIL

Express Mail Mailing Label Number: EV247989557US
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I hereby certify that this correspondence is being deposited with the United States Postal Service Express Mail Post Office to Addressee service under 37 C.F.R. §1.10 on the date indicated above and is addressed to the Commissioner of Patents and Trademarks, Alexandria, VA 22313-1450.

Dated: September 11, 2003


Leslie S. Szivos, Ph.D.